ΡΛΝ	ĴΪΤ
	SEMI CONDUCTOR

30V P-Channel Enhancement Mode MOSFET

Voltage

-45 A Current

Features

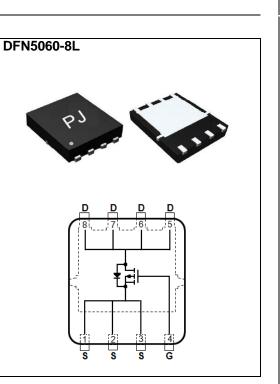
• R_{DS(ON)}, V_{GS}@-10V,I_D@-10A<15.5mΩ

-30 V

- $R_{DS(ON)}, V_{GS}@-4.5V, I_D@-6A<23m\Omega$ •
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case: DFN5060-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0028 ounces, 0.08 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETE	R	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	-30	V	
Gate-Source Voltage		V _{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	- I _D	-45	A	
	T _c =100°C		-28		
Pulsed Drain Current ^(Note 1)	T _c =25°C	I _{DM}	-180		
Power Dissipation	T _C =25°C	Po	40	W	
	T _c =100°C		16		
Continuous Drain Current	T _A =25°C	I _D	-10	A	
	T _A =70°C		-8		
Power Dissipation	T _A =25°C		2.0	14/	
Power Dissipation	T _A =70°C	PD	1.3	W	
Operating Junction and Storage	Temperature Range	T _J ,T _{STG}	-55~150	°C	
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	R _{θJC}	3.1	°C/W	
	Junction to Ambient	R _{θJA}	62.5		

imited only By Maximum Junction Temperature



Electrical Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static	0111202					00
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =-250uA	-30	-	-	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=-250$ uA	-1.0	-1.6	-2.5	V
Drain-Source On-State Resistance		V _{GS} =-10V,I _D =-10A	-	12	15.5	mΩ
	R _{DS(on)}	V _{GS} =-4.5V,I _D =-6A	-	18	23	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V,V _{GS} =0V	-	-	-1.0	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 6)						
Total Gate Charge	Qg	V _{DS} =-15V, I _D =-8A, V _{GS} =-4.5V ^(Note 1,2)	-	14	-	nC
Gate-Source Charge	Q_{gs}		-	4.6	-	
Gate-Drain Charge	Q_gd		-	5.4	-	
Input Capacitance	Ciss	V _{DS} =-15V, V _{GS} =0V, f=1.0MHZ	-	1556	-	pF
Output Capacitance	Coss		-	243	-	
Reverse Transfer Capacitance	Crss		-	175	-	
Turn-On Delay Time	td _(on)	V _{DD} =-15V, I _D =-1A, V _{GS} =-10V, R _G =6Ω	-	7.3	-	
Turn-On Rise Time	t _r		-	13	-	ns
Turn-Off Delay Time	td _(off)		-	88	-	
Turn-Off Fall Time	t _f		-	48	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	1				45	A
Diode Forward Current	I _S		-	-	-45	
Diode Forward Voltage	V_{SD}	I _S =-1A,V _{GS} =0V	-	-0.7	-1	V

NOTES :

- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics
- Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited
- 5. Reua is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing

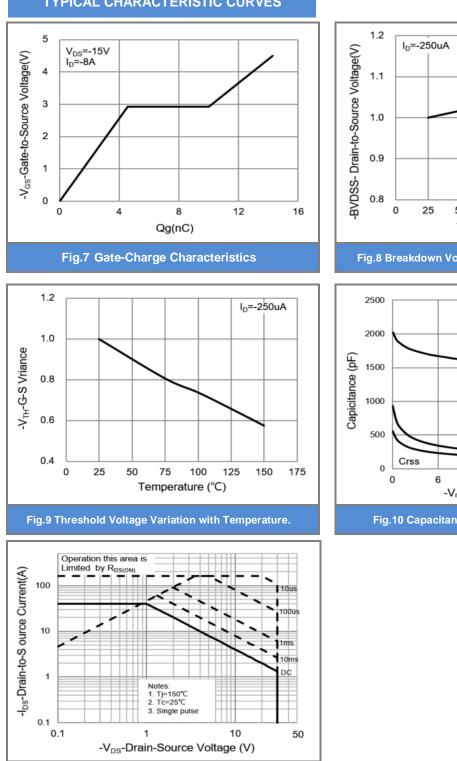


PJQ5411 TYPICAL CHARACTERISTIC CURVES 20 20 V_{DS}=-5V -10V,-8V,-5V,-4.5V -I_{DS}-Drain-to-S ource Current(A) -I_{DS}-Drain-to-S ource Current(A) 15 V_{GS}=-3V 15 10 10 T**J=125°**C V_{GS}=-2.5V T_J=25℃ 5 5 0 0 0 1 2 3 4 5 0 1 2 3 4 5 -V_{DS}- Drain-to-Source Voltage(V) -V_{GS}-Gate-to-Source Voltage(V) **Fig.2 Transfer Characteristics Fig.1 On-Region Characteristics** 25 2.0 R_{Ds}(on)- On-Resistance (Normalized) R_{Ds}(on)- On-Resistance(mΩ) 20 V_{GS}=-4.5V 1.6 V_{GS}=-10V, I_D=-10A 15 1.2 V_{GS}=-10V V_{GS}=-4.5V, I_D=-6A 10 0.8 5 0.4 0 5 10 15 20 25 0 50 75 100 125 150 175 Temperature (°C) -I_{DS}-Drain-to-Source Current(A) Fig.4 On-Resistance vs. Junction temperature Fig.3 On-Resistance vs. Drain Current 40 10 I_D=-5A $R_{DS}(on)$ - On-Resistance(m Ω) -I_{sp}-Source to Drain Current(A) 30 1 T_i=125℃ 20 0.1 Tj=125℃ T_i=25℃ 10 Ti=25℃ 0 0.01 0 2 4 6 10 8 0 0.3 1.2 0.6 0.9 -V_{SD}-Source-to-Drain Voltage(V) -V_{GS}-Gate-to-Source Voltage(V)

Fig.5 On-Resistance Variation with VGS.

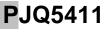
Fig.6 Body Diode Characteristics

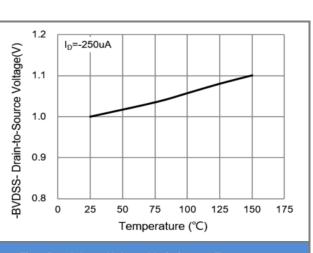
Fig.11 Maximum Safe Operating Area













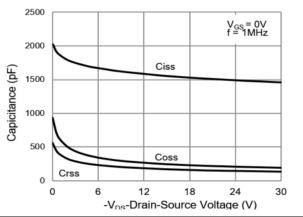


Fig.10 Capacitance vs. Drain-Source Voltage.

SEMI CONDUCTOR

PANJ



March 23,2018-REV.01





$$\begin{split} & \mathsf{T}_{\mathsf{J},\mathsf{PK}} \texttt{=} \mathsf{Tc} \texttt{+} \mathsf{P}_{\mathsf{DM}} \texttt{*} \mathsf{Z}_{\mathsf{TH} \texttt{-} \mathsf{JC}} \texttt{*} \mathsf{R}_{\mathsf{TH} \texttt{-} \mathsf{JC}} \\ & \mathsf{R}_{\mathsf{TH} \texttt{-} \mathsf{JC}} \texttt{=} \texttt{3.1}^\circ \mathsf{C} / \mathsf{W} \\ & \mathsf{Tc} \texttt{=} \texttt{25}^\circ \mathsf{C} \end{split}$$

Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

ZTH-JC Normalized Transient Thermal Impedance

PJQ5411

1

0.1

0.01

D=0.5

0.2

0.05

TYPICAL CHARACTERISTIC CURVES

10

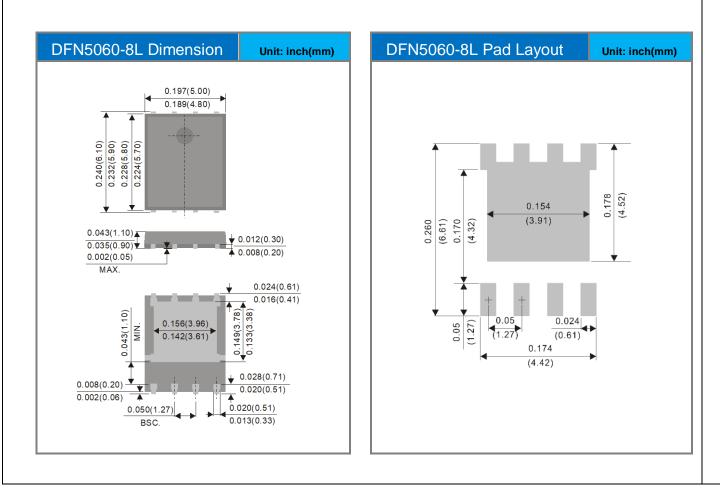




Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJQ5411_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5411	Halogen free

Packaging Information & Mounting Pad Layout





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